

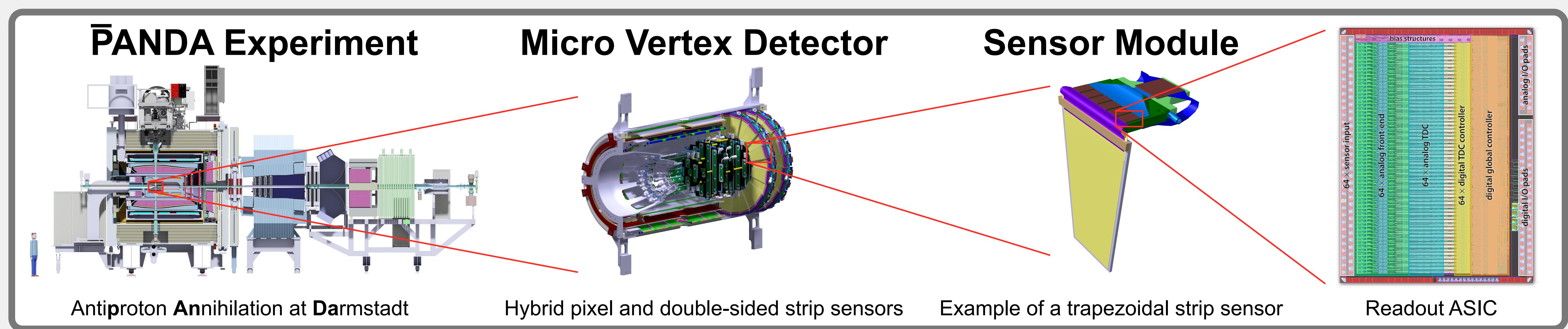
# A Time-Based Front-End ASIC for the Silicon Micro Strip Sensors of the PANDA Micro Vertex Detector

Valentino Di Pietro<sup>1</sup>, Kai-Thomas Brinkmann<sup>1</sup>, Alberto Riccardi<sup>1</sup>, James Ritman<sup>3</sup>,  
Angelo Rivetti<sup>2</sup>, Manuel Rolo<sup>2</sup>, Tobias Stockmanns<sup>3</sup>, André Zambanini<sup>3</sup>

<sup>1</sup> II. Physikalisches Institut, Justus-Liebig-Universität Gießen

<sup>2</sup> INFN, Sezione di Torino

<sup>3</sup> Forschungszentrum Jülich



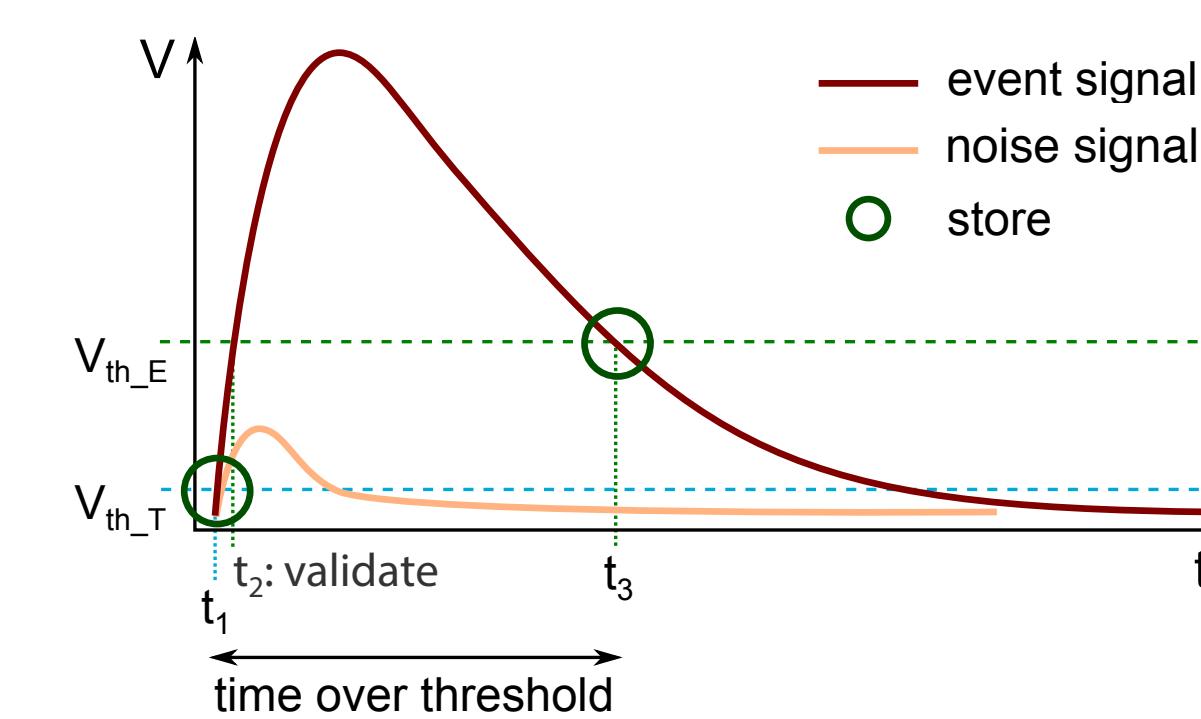
## PANDA Strip ASIC (PASTA)

- Channels (input pitch) 64 (63 µm)
- Technology CMOS 110 nm
- Rate capability 100 kHz/ch
- Power consumption < 4 mW/ch
- Front-end noise < 600 e<sup>-</sup>
- Time bin width 50-400 ps
- Charge resolution 8 bit (dyn. range)\*
- Radiation dose 100 kGy\*

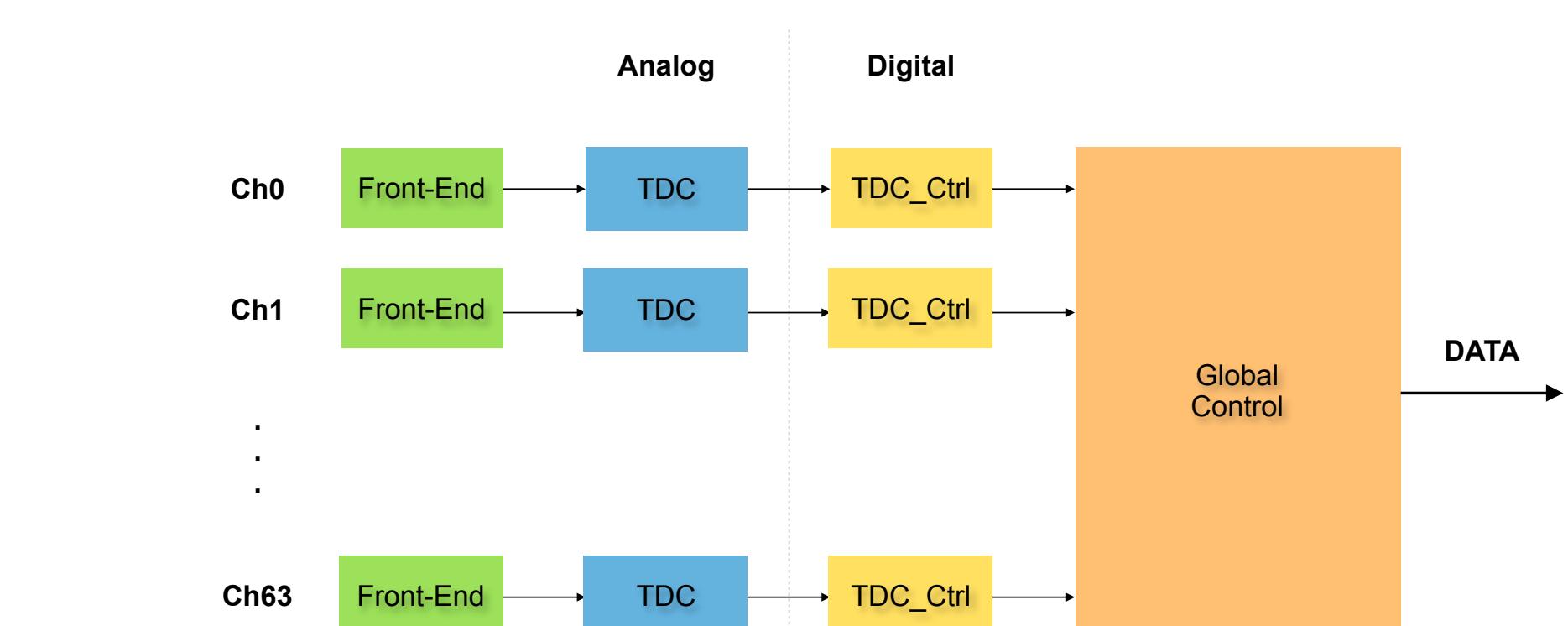
\* Design Goal

## Measurement Concept

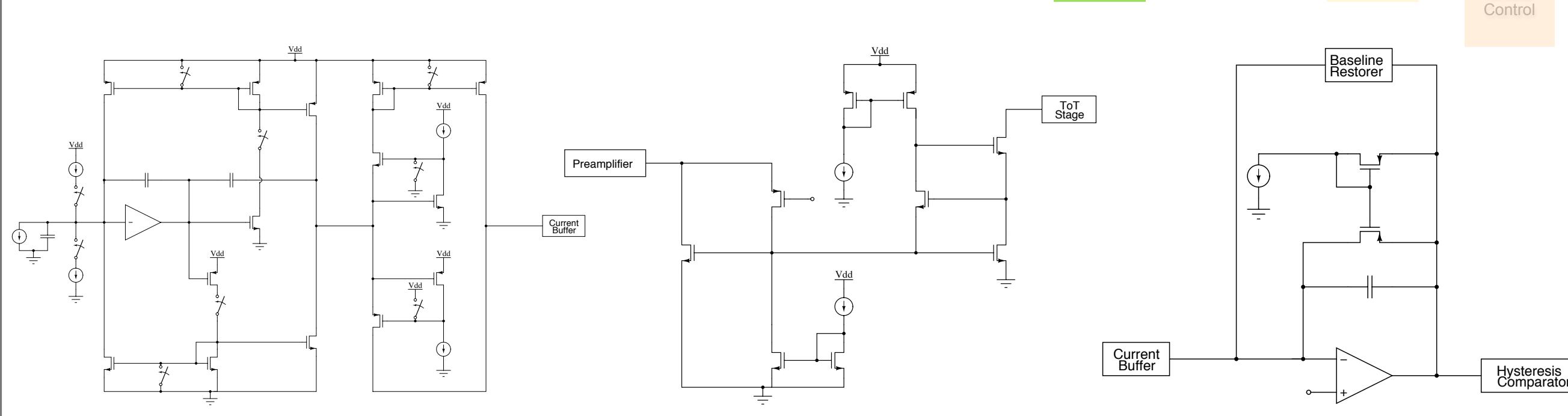
Inspired by TOFPET



## ASIC Architecture



## Front-End Architecture



### Preamplifier

First amplification stage capable of processing signals of both polarities (n-type or p-type strips)

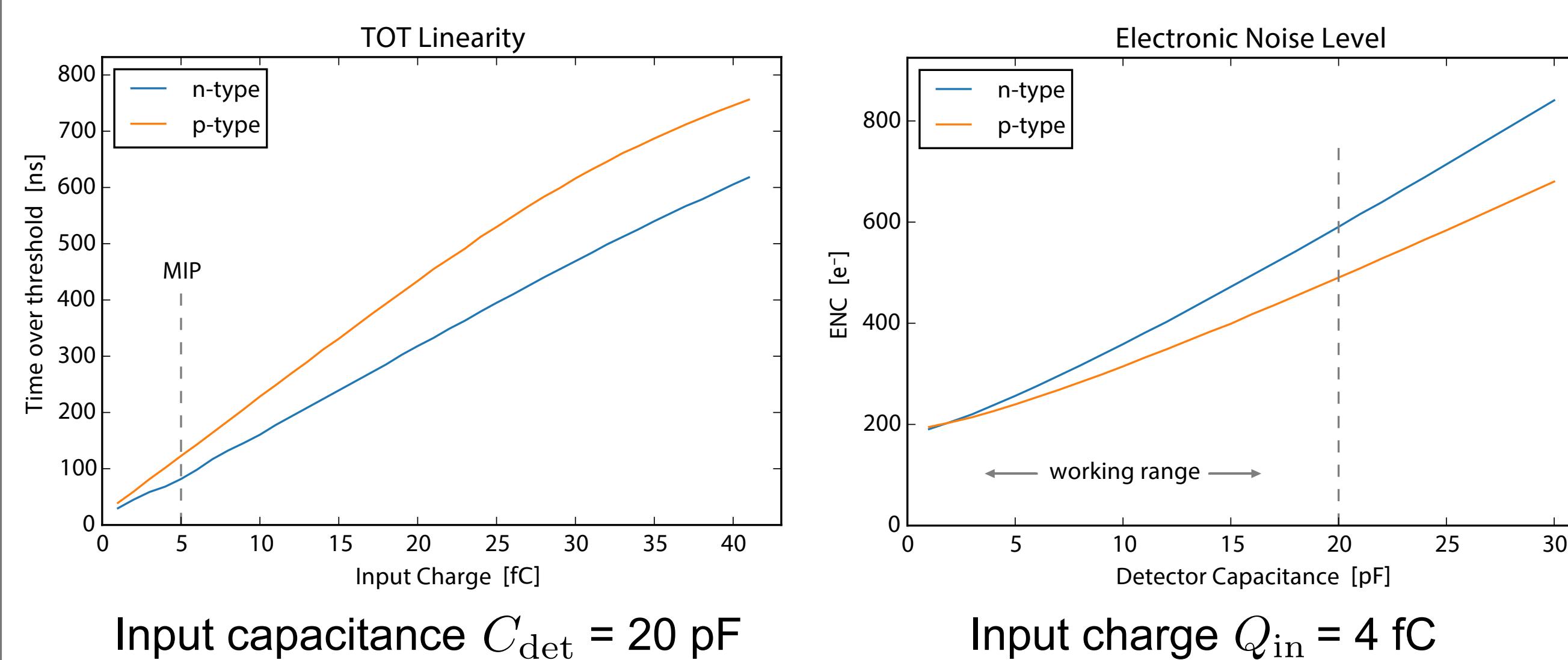
### Current Buffer

Stage providing both current gain and impedance adjustment

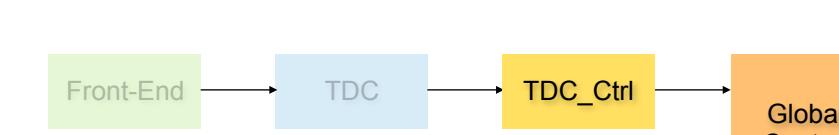
### ToT Amplifier

Second amplification stage for the linear discharge of the feedback capacitance

## Simulations

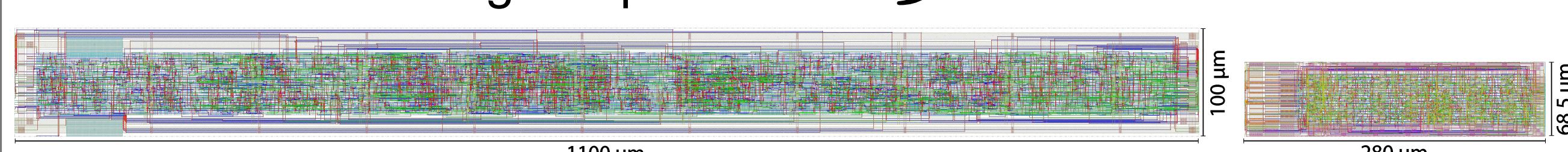


## Digital Blocks



### Optimization of the TDC Control

- Size reduced by ~80%
  - Overall power consumption halved
  - Radiation-hard logic implemented
- } compared with TOFPET



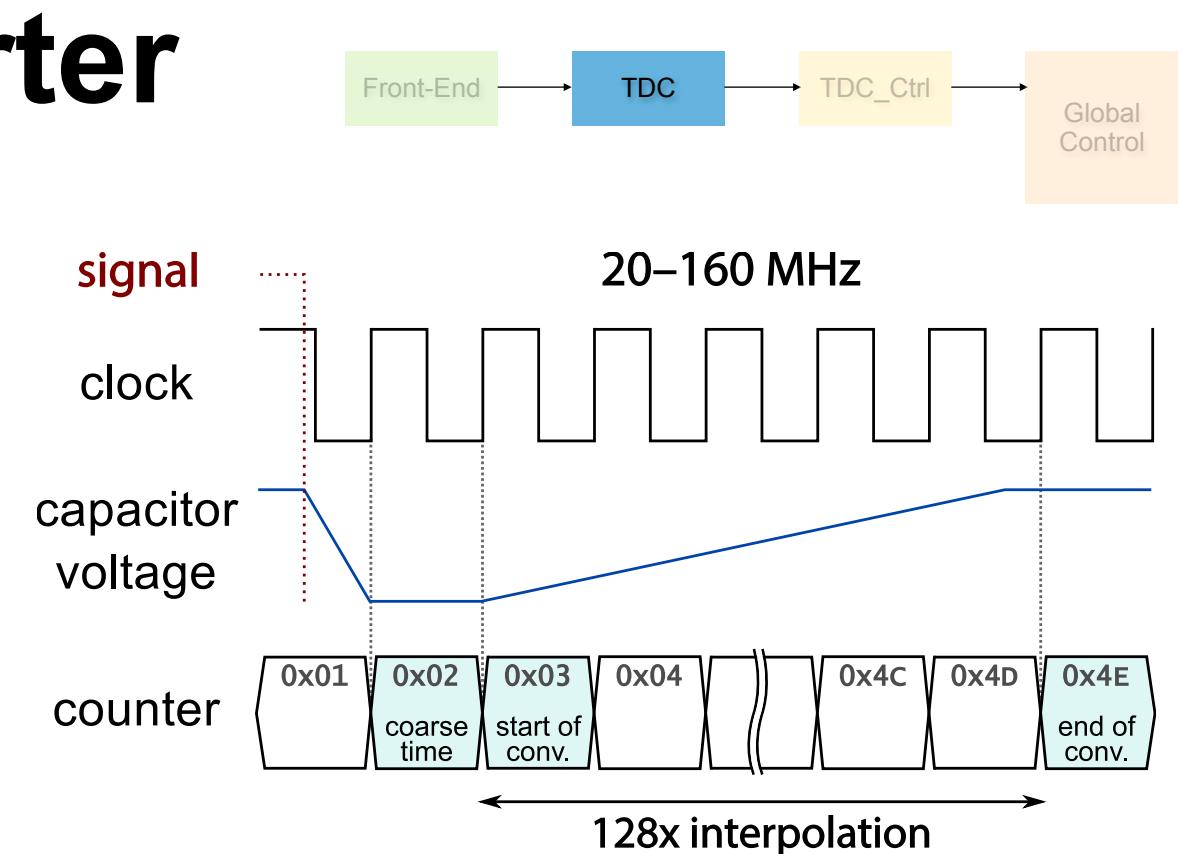
### Single Event Upset (SEU) Protection

- 1 bit: Triple Modular Redundancy
- n bits: Hamming encoding

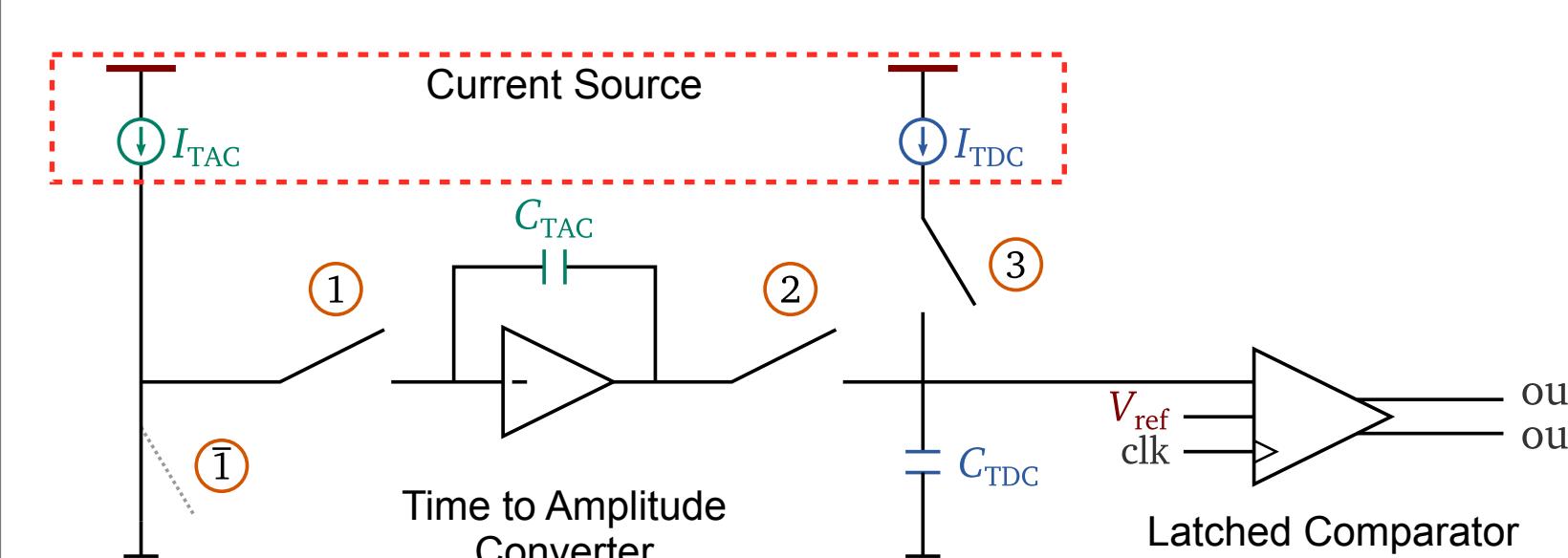
## Time to Digital Converter

### Motivation

- High temporal precision
- Low power consumption
- Compact structure



### Architecture



**Current Source**  
Block providing a fine tuning system for  $I_{TDC}$  in order to fix the ratio of the two currents and secure the desired resolution

### Time Amplification

The time of conversion  $t_{TDC}$  can be calculated as follows:

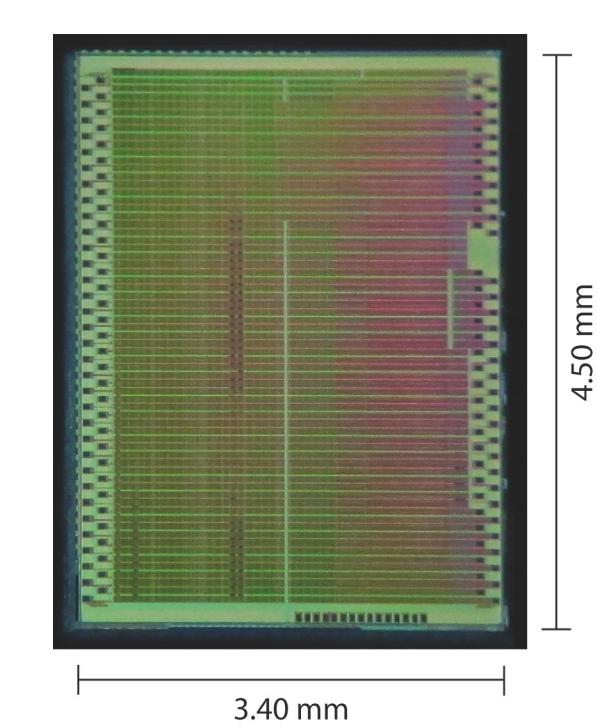
$$C_{TDC} = 4 \cdot C_{TAC}$$

$$I_{TDC} = 1/32 \cdot I_{TAC}$$

$$V_{TDC} = V_{TAC} \iff \frac{I_{TDC} \cdot t_{TDC}}{C_{TDC}} = \frac{I_{TAC} \cdot t_{TAC}}{C_{TAC}} \implies t_{TDC} = 128 \cdot t_{TAC}$$

## Conclusions

- Chip designed according to the given specifications
- Analog, digital, and mixed-mode simulations extensively studied
- Project submitted in April 2015
- Prototypes delivered in September 2015



## Perspectives

- Readout system under development
- PCB design started
- Beam test planned for early 2016